[Claims]

[Claim 1]

A semiconductor device comprising:

a stacked body including a first electrode layer and a second electrode layer provided to be electrically insulated from the first electrode layer in a stacking direction;

at least two first insulating layers provided in the stacked body to penetrate from an upper end of the stacked body to a lower end of the stacked body, and extending in a first direction intersecting the stacking direction;

a first staircase portion provided in a first end region of the stacked body between the at least two first insulating layers;

a second staircase portion provided in a second end region of the stacked body located on a side opposite to the first end region between the at least two first insulating layers; and

a second insulating layer extending in the first direction, provided in the stacked body between the at least two first insulating layers, and dividing the second electrode layer in a second direction intersecting the stacking direction and the first direction, the second insulating layer not dividing the first electrode layer,

a length in the first direction of the second insulating layer being longer than a length in the first direction of the second electrode layer and shorter than a length in the first direction of the first electrode layer, and

the first electrode layer is a dummy word line.

[Claim 2]

The device according to claim 1, wherein

the second electrode layer is a selection gate layer.

[Claim 3]

The device according to claim 1, wherein

the stacked body includes a first column-shaped portion

provided in an intermediate region of the stacked body located between the first end region and the second end region, the first column-shaped portion extending in the stacking direction, and

the first column-shaped portion includes:

a semiconductor body extending in the stacking direction; and

a charge storage portion provided between the semiconductor body and the first electrode layer.